# AON6428L

## 30V N-Channel MOSFET

ALPHA & OMEGA SEMICONDUCTOR

## General Description

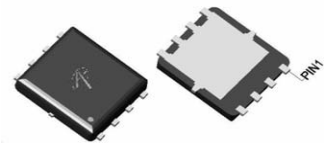
The AON6428L uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge.This device is suitable for use as a high side switch in SMPS and general purpose applications.

## Product Summary

| | |
|---|---|
| $V_{DS}$ | 30V |
| $I_D$ (at $V_{GS}$=10V) | 24A |
| $R_{DS(ON)}$ (at $V_{GS}$=10V) | < 10mΩ |
| $R_{DS(ON)}$ (at $V_{GS}$= 4.5V) | < 14.5mΩ |

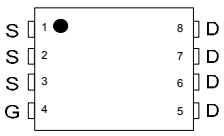
100% UIS Tested
100% $R_g$ Tested

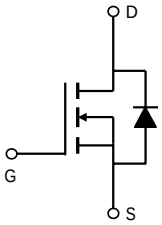
Green Product




DFN5X6

Top View




**Absolute Maximum Ratings $T_A$=25°C unless otherwise noted**

| Parameter | | Symbol | Maximum | Units |
|---|---|---|---|---|
| Drain-Source Voltage | | $V_{DS}$ | **30** | V |
| Gate-Source Voltage | | $V_{GS}$ | **±20** | V |
| Continuous Drain Current [G] | $T_C$=25°C | $I_D$ | **24** | A |
| | $T_C$=100°C | | **19** | |
| Pulsed Drain Current [C] | | $I_{DM}$ | **80** | |
| Continuous Drain Current | $T_A$=25°C | $I_{DSM}$ | **11** | A |
| | $T_A$=70°C | | **8** | |
| Avalanche Current [C] | | $I_{AR}$ | **20** | A |
| Repetitive avalanche energy L=0.1mH [C] | | $E_{AR}$ | **20** | mJ |
| Power Dissipation [B] | $T_C$=25°C | $P_D$ | **25** | W |
| | $T_C$=100°C | | **10** | |
| Power Dissipation [A] | $T_A$=25°C | $P_{DSM}$ | **2** | W |
| | $T_A$=70°C | | **1.3** | |
| Junction and Storage Temperature Range | | $T_J$, $T_{STG}$ | **-55 to 150** | °C |

**Thermal Characteristics**

| Parameter | | Symbol | Typ | Max | Units |
|---|---|---|---|---|---|
| Maximum Junction-to-Ambient [A] | t ≤ 10s | $R_{\theta JA}$ | 21 | 25 | °C/W |
| Maximum Junction-to-Ambient [A D] | Steady-State | | 50 | 60 | °C/W |
| Maximum Junction-to-Case | Steady-State | $R_{\theta JC}$ | 3.5 | 5 | °C/W |

**Electrical Characteristics ($T_J$=25°C unless otherwise noted)**

| Symbol | Parameter | Conditions | Min | Typ | Max | Units |
|---|---|---|---|---|---|---|
| **STATIC PARAMETERS** | | | | | | |
| $BV_{DSS}$ | Drain-Source Breakdown Voltage | $I_D$=250µA, $V_{GS}$=0V | 30 | | | V |
| $I_{DSS}$ | Zero Gate Voltage Drain Current | $V_{DS}$=30V, $V_{GS}$=0V | | | 1 | µA |
| | | $T_J$=55°C | | | 5 | |
| $I_{GSS}$ | Gate-Body leakage current | $V_{DS}$=0V, $V_{GS}$= ±20V | | | ±100 | nA |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS}$=$V_{GS}$ $I_D$=250µA | 1.2 | 1.7 | 2.2 | V |
| $I_{D(ON)}$ | On state drain current | $V_{GS}$=10V, $V_{DS}$=5V | 80 | | | A |
| $R_{DS(ON)}$ | Static Drain-Source On-Resistance | $V_{GS}$=10V, $I_D$=20A | | 8.3 | 10 | mΩ |
| | | $T_J$=125°C | | 12.4 | 15 | |
| | | $V_{GS}$=4.5V, $I_D$=20A | | 11.3 | 14.5 | mΩ |
| $g_{FS}$ | Forward Transconductance | $V_{DS}$=5V, $I_D$=20A | | 43 | | S |
| $V_{SD}$ | Diode Forward Voltage | $I_S$=1A,$V_{GS}$=0V | | 0.7 | 1 | V |
| $I_S$ | Maximum Body-Diode Continuous Current | | | | 25 | A |
| **DYNAMIC PARAMETERS** | | | | | | |
| $C_{iss}$ | Input Capacitance | $V_{GS}$=0V, $V_{DS}$=15V, f=1MHz | 620 | 770 | 920 | pF |
| $C_{oss}$ | Output Capacitance | | 170 | 240 | 310 | pF |
| $C_{rss}$ | Reverse Transfer Capacitance | | 45 | 77 | 110 | pF |
| $R_g$ | Gate resistance | $V_{GS}$=0V, $V_{DS}$=0V, f=1MHz | 0.4 | 0.8 | 1.4 | Ω |
| **SWITCHING PARAMETERS** | | | | | | |
| $Q_g$(10V) | Total Gate Charge | $V_{GS}$=10V, $V_{DS}$=15V, $I_D$=20A | 11.8 | 14.8 | 17.8 | nC |
| $Q_g$(4.5V) | Total Gate Charge | | 5.7 | 7.1 | 8.5 | nC |
| $Q_{gs}$ | Gate Source Charge | | 1.7 | 2.2 | 2.6 | nC |
| $Q_{gd}$ | Gate Drain Charge | | 1.8 | 3.1 | 4.3 | nC |
| $t_{D(on)}$ | Turn-On DelayTime | $V_{GS}$=10V, $V_{DS}$=15V, $R_L$=0.75Ω, $R_{GEN}$=3Ω | | 5 | | ns |
| $t_r$ | Turn-On Rise Time | | | 3 | | ns |
| $t_{D(off)}$ | Turn-Off DelayTime | | | 18 | | ns |
| $t_f$ | Turn-Off Fall Time | | | 3 | | ns |
| $t_{rr}$ | Body Diode Reverse Recovery Time | $I_F$=20A, dI/dt=500A/µs | 9 | 11 | 13 | ns |
| $Q_{rr}$ | Body Diode Reverse Recovery Charge | $I_F$=20A, dI/dt=500A/µs | 18 | 23 | 28 | nC |

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in$^2$ FR-4 board with 2oz. Copper, in a still air environment with $T_A$ =25°C. The Power dissipation $P_{DSM}$ is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.

B. The power dissipation $P_D$ is based on $T_{J(MAX)}$=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150°C. Ratings are based on low frequency and duty cycles to keep initial $T_J$ =25°C.

D. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to case $R_{\theta JC}$ and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300µs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedence which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=150°C. The SOA curve provides a single pulse rating.

G. The maximum current rating is limited by bond-wires.

H. These tests are performed with the device mounted on 1 in$^2$ FR-4 board with 2oz. Copper, in a still air environment with $T_A$=25°C.

Rev 1: April 2009

## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

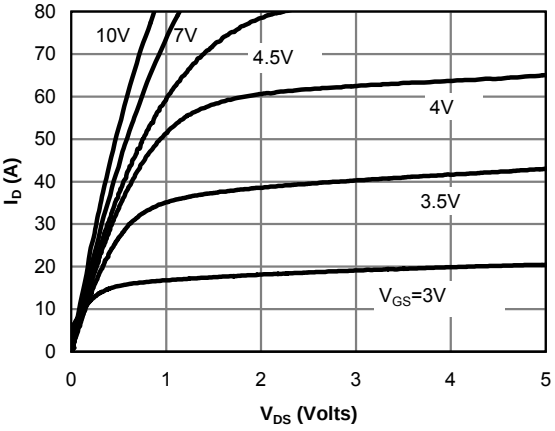



**Fig 1: On-Region Characteristics (Note E)**

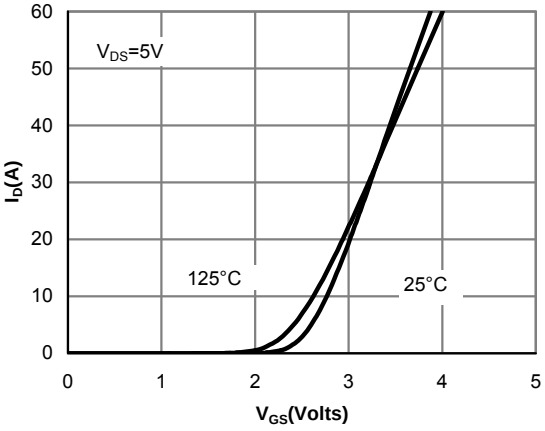



**Figure 2: Transfer Characteristics (Note E)**

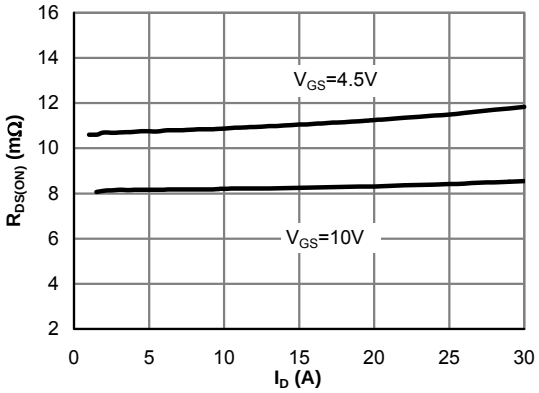



**Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)**

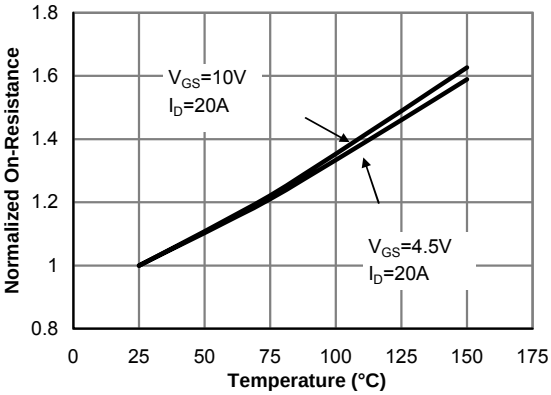



**Figure 4: On-Resistance vs. Junction Temperature (Note E)**

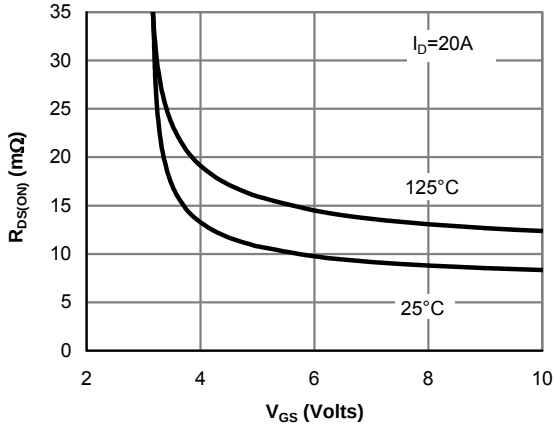



**Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)**

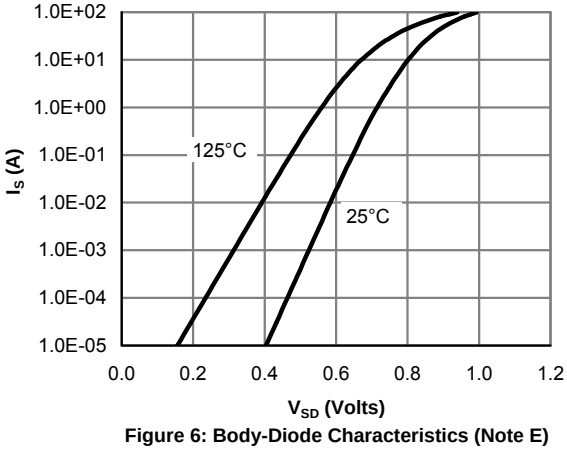



**Figure 6: Body-Diode Characteristics (Note E)**

## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

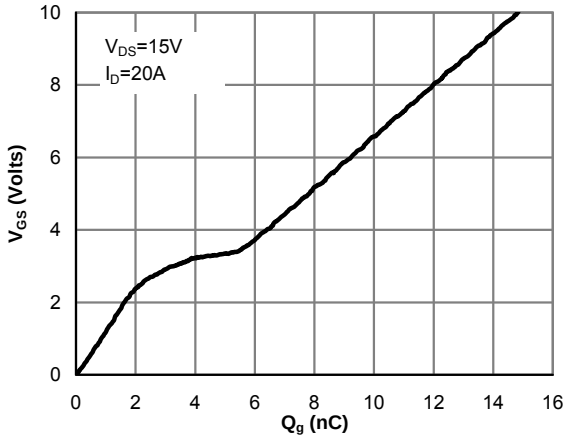



**Figure 7: Gate-Charge Characteristics**

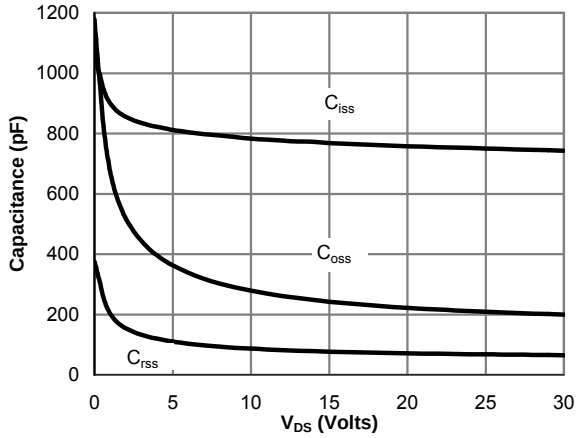



**Figure 8: Capacitance Characteristics**

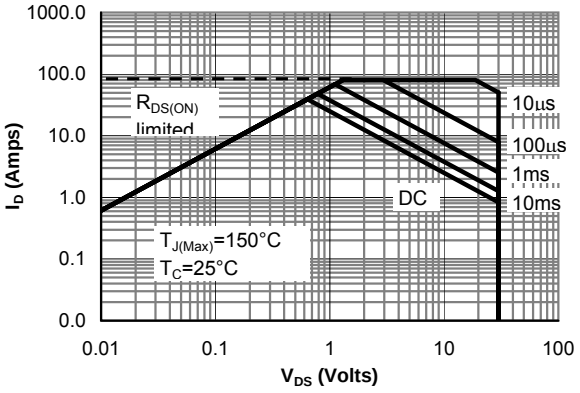



**Figure 9: Maximum Forward Biased Safe Operating Area (Note F)**

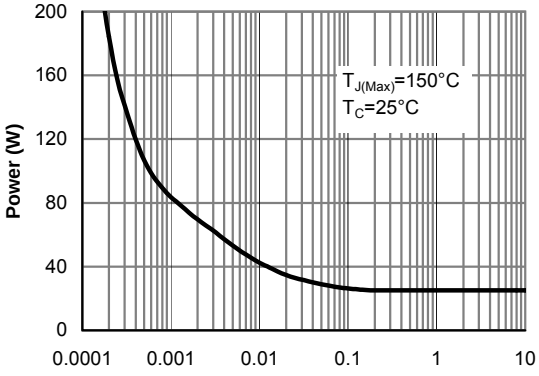



**Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)**

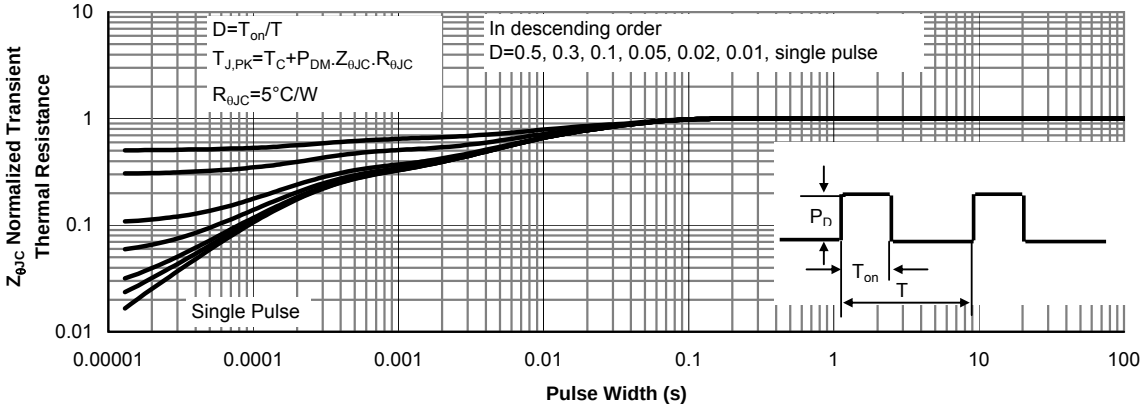



**Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)**

## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

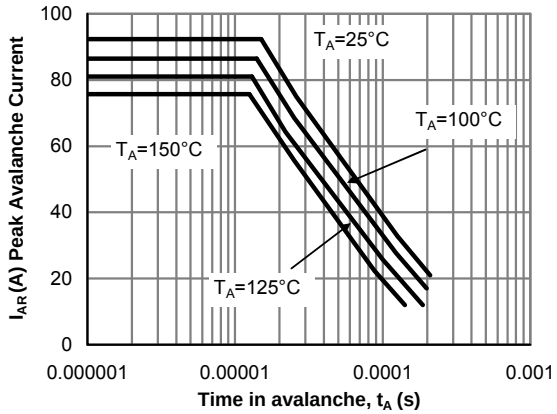



**Figure 12: Single Pulse Avalanche capability (Note C)**

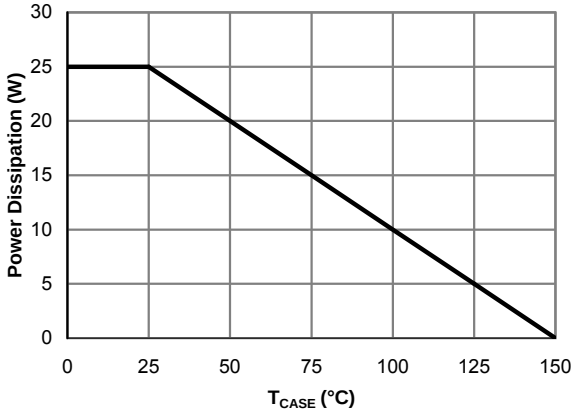



**Figure 13: Power De-rating (Note F)**

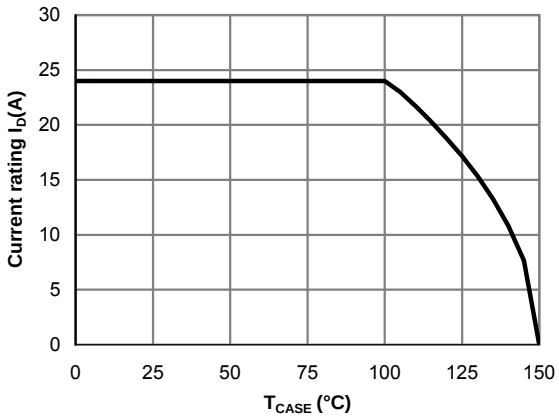



**Figure 14: Current De-rating (Note F)**

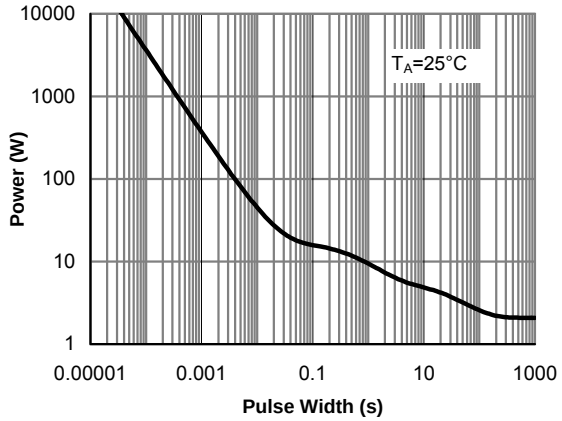



**Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)**

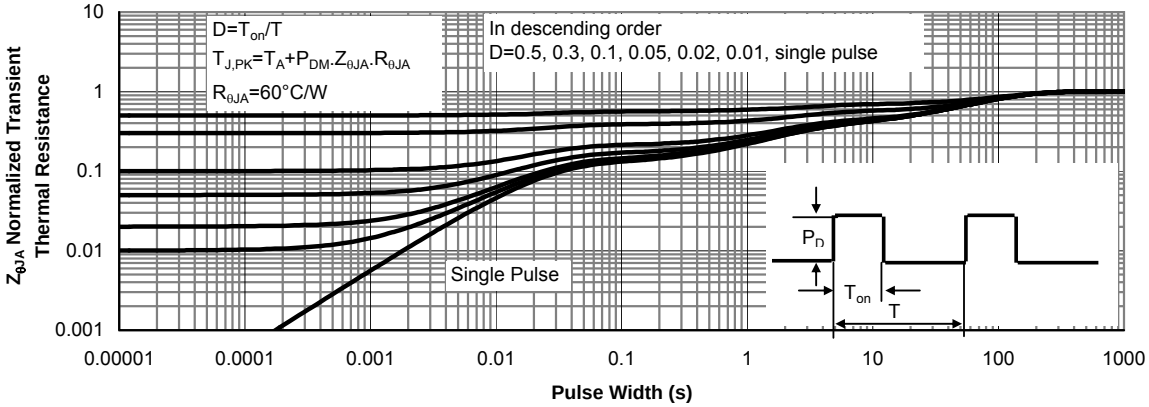
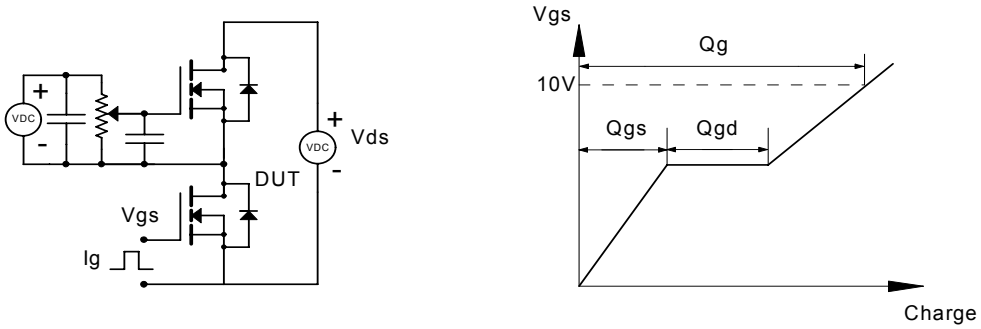
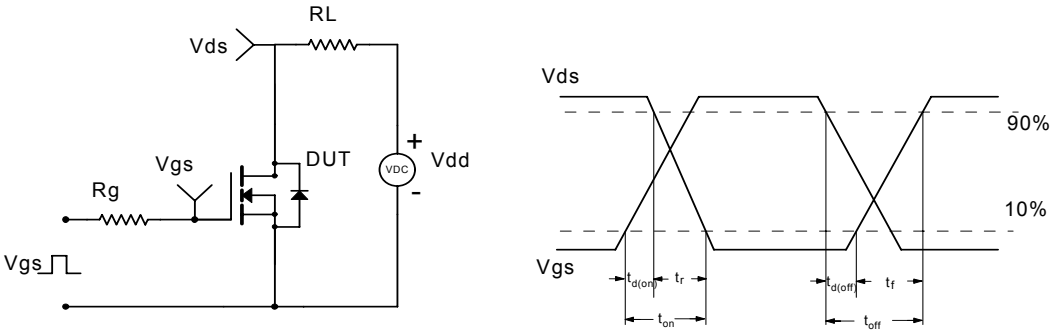



**Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)**

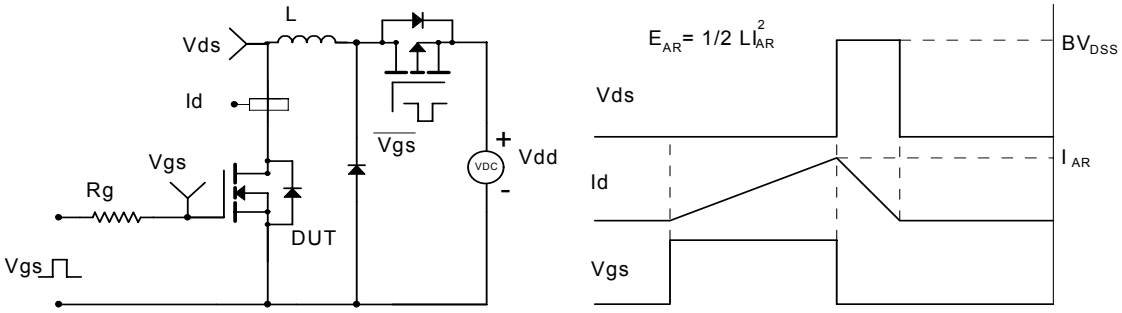
## Gate Charge Test Circuit & Waveform




## Resistive Switching Test Circuit & Waveforms




## Unclamped Inductive Switching (UIS) Test Circuit & Waveforms




## Diode Recovery Test Circuit & Waveforms